

# Dual-Polarization Topological Interface States in Ridge Photonic Crystals

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Cite This: <https://doi.org/10.1021/acsphotonics.4c00248>

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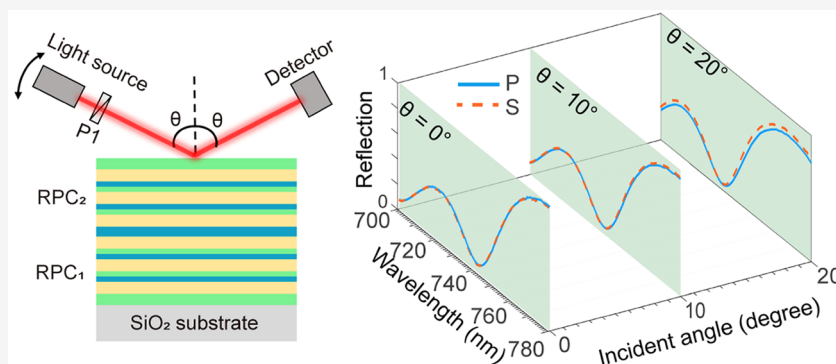
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**ABSTRACT:** Lifting the nodal ring degeneracy can result in topologically nontrivial ridge bulk states and associated interface states, which have been realized by 1D photonic crystals. However, the ridge interface states exist only for p polarization, which limits their potential applications in polarization-independent optical devices. Here, a scheme to design the polarization-independent nodal ring using a 1D photonic crystal is proposed. It is revealed that the fourfold degeneracy exactly lies at the position where the absentee layer condition is satisfied for each layer. Once the absentee layer condition cannot be satisfied for each layer, the nodal ring will be gapped, accompanied by ridge interface states traversing the gap. Interestingly, these p-polarized and s-polarized ridge interface states are degenerate almost in the whole band gap, which facilitates polarization-independent optical filtering. This work proposes a novel way for polarization-independent optical filtering and associated applications, such as high-efficiency solar energy conversion and privacy screen.

**KEYWORDS:** ridge photonic crystals, nodal ring, topological interface states, dual polarization

## INTRODUCTION

Photonic topological states in three-dimensional (3D) momentum space possess rich physical properties and interesting phenomena,<sup>1,2</sup> such as robust surface transport<sup>3,4</sup> and negative refraction of surface waves.<sup>5,6</sup> In general, the 3D topological states can be divided into two classes. One of them is the gapped topological states,<sup>7–9</sup> such as 3D photonic topological insulators.<sup>4,10</sup> Another class is the gapless topological states<sup>11–18</sup> (i.e., photonic topological semimetals), such as nodal rings<sup>19,20</sup> (a ring-shaped line degeneracy). Topological semimetals can serve as the parent states of various kinds of gapped topological states and have attracted much interest. For example, by breaking the symmetry of the system, a nodal ring degeneracy can transit to a topologically nontrivial ridge state.<sup>21,22</sup> So far, researchers have successfully observed the nodal ring degeneracy in metallic photonic crystals (PCs) and metacrystals.<sup>19,23</sup> However, these carefully designed artificial periodic structures are usually very complex, hindering their applications in nanoscale photonic systems.

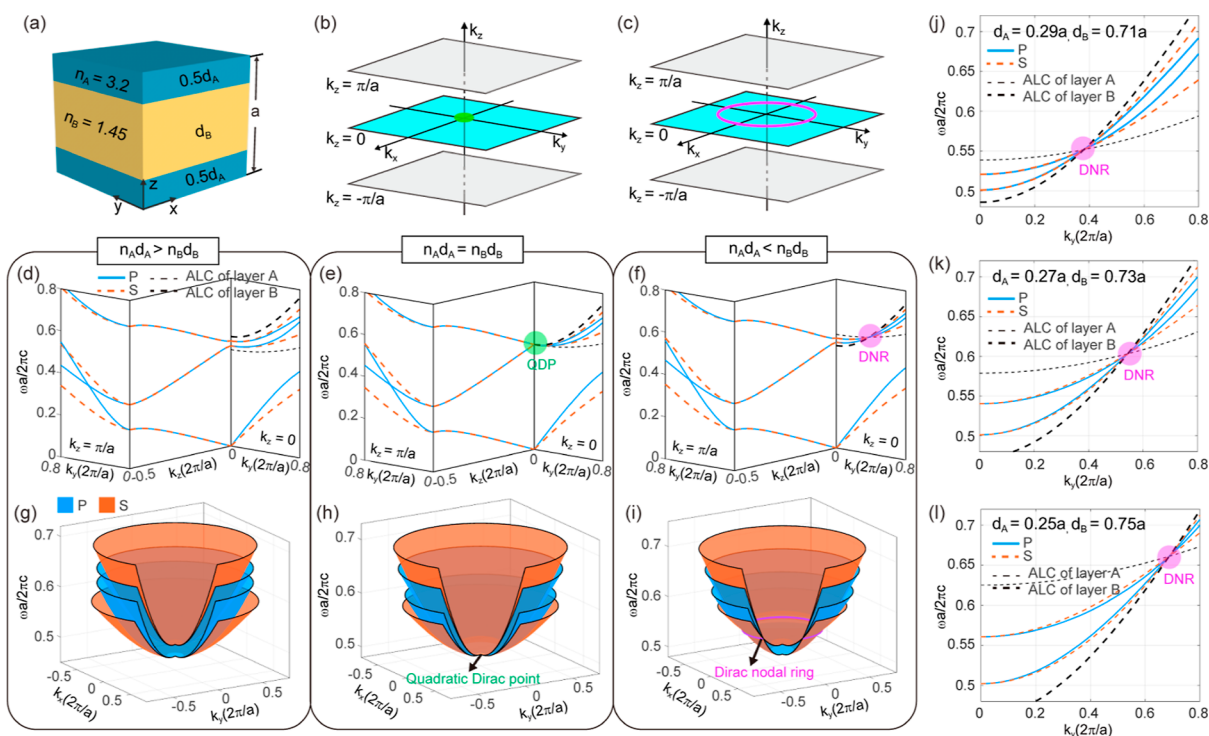
To overcome these issues, researchers have started to explore the topological nodal ring degeneracy in simple

structures. In theory, researchers have pointed out that a 2-fold degenerate nodal ring can exist in a 1D PC composed of anisotropic dielectrics<sup>24</sup> or design various types of 4-fold degenerate nodal ring by a 1D hypercrystal.<sup>25</sup> Recently, researchers have experimentally demonstrated that a 4-fold degenerate nodal ring can be realized simply by a 1D PC composed of isotropic dielectrics.<sup>26</sup> Meanwhile, we have experimentally observed a 2-fold degenerate nodal ring in a 1D dielectric PC and the associated ridge interface states by lifting the nodal ring degeneracy.<sup>22</sup> However, these ridge interface states exist only for p polarization, which imposes constraints on their potential applications in polarization-independent optical filters and associated devices.

**Received:** February 7, 2024

**Revised:** May 15, 2024

**Accepted:** May 16, 2024



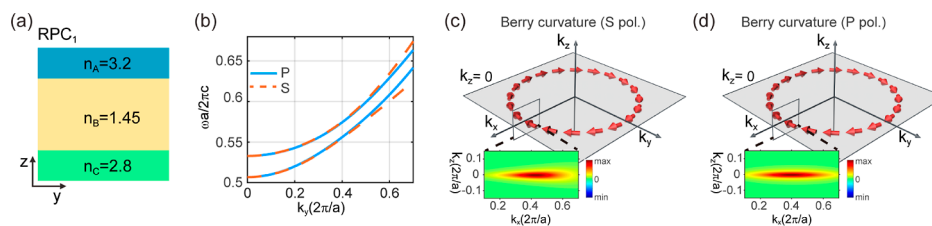
**Figure 1.** Design of dual-polarization DNR in a 1D PC. (a) Inversion symmetric unit cell of a 1D PC, which consists of three dielectric layers (A/B/A). The refractive index and thickness of layer A (B) are 3.2 (1.45) and  $d_A$  ( $d_B$ ), respectively. (b,c) 3D Brillouin zone of the 1D PC. The cyan plane highlights the  $k_x$ - $k_y$  plane at  $k_z = 0$ . The green circle in (b) marks the position of a QDP. The purple circle in (c) marks a dual-polarization nodal ring. (d) P-polarized (light-blue solid lines) and s-polarized (orange dashed lines) band structures along the  $k_z$  and  $k_y$  directions when  $d_A = 0.34a$  and  $d_B = 0.66a$ . The black thin dashed line and thick dashed line represent the absentee layer condition for layer A and layer B, respectively. There is not any 4-fold degenerate point in the band structures. (g) 3D band structures on the  $k_z = 0$  plane. For a better view of the degeneracy, only three-quarters of the bands are shown. (e,h) Similar to (d) and (g), but for the case of  $d_A = 0.3118a$  and  $d_B = 0.6882a$ . In this case, the quarter-wave stack condition  $n_A d_A = n_B d_B$  is satisfied. The green circle highlights the QDP. (f,i) Similar to (d) and (g), but for the case of  $d_A = 0.29a$  and  $d_B = 0.71a$ . The purple circle highlights the position of DNR. (j) Band along  $k_y$  direction when  $d_A = 0.29a$  and  $d_B = 0.71a$ . (k,l) Similar to (j) but for the case of  $d_A = 0.27a$ ,  $d_B = 0.73a$  and  $d_A = 0.25a$ ,  $d_B = 0.75a$ , respectively.

In this work, starting from a quarter-wave stack, a method to design a dual-polarization nodal ring in a 1D PC is proposed. We reveal that the existence of these fourfold degeneracies can be understood from the perspective of absentee layer conditions in thin-film optics. By changing the refractive index of one layer in the unit cell, the absentee layer condition cannot be simultaneously satisfied for each layer, so that the nodal ring will be gapped and transit to nontrivial ridge states, manifested as localized Berry vortices. The existence of dual-polarization ridge interface states is experimentally observed, and we find that p-polarized and s-polarized interface bands are degenerate almost in the whole band gap. Our work makes it possible to realize a polarization-independent optical filter and associated devices using 1D PCs.

## RESULTS AND DISCUSSION

Although a nodal ring for single polarization (based on the principle of Brewster angle, a single-polarization effect) has been reported in ref 22, the present work studies the dual-polarization nodal ring and relevant topological interface states. Note that a prerequisite for dual-polarization ridge states is the existence of a dual-polarization nodal ring. It seems that a simple way to achieve a dual-polarization nodal ring is to fine-tune the structural parameters of 1D PCs to have an accidentally double-degenerate nodal ring, e.g., by using dual-symmetric ( $\epsilon = \mu$ ) materials. But this is unrealistic for most natural materials. Here, we start by introducing the method to

design a dual-polarization nodal ring using all-dielectric materials. We consider a 1D PC consisting of alternating layer A ( $n_A = 3.2$ ) and layer B ( $n_B = 1.45$ ), as shown in Figure 1a. Their thicknesses are  $d_A$  and  $d_B$ , respectively. Apart from Bloch wavevector  $k_z$ , we take in-plane components  $k_x$  and  $k_y$  into account to construct a 3D momentum space. The 3D Brillouin zone of this 1D PC is bounded only in the  $k_z$ -direction by two planes of  $k_z = \pm \pi/a$  because this 1D PC has discrete translational symmetry only in the  $z$ -direction, as shown in Figure 1b. Besides, such 1D PC is isotropic and has continuous translational symmetry on the  $xy$ -plane, indicating that its dispersion relations along any radial direction are identical. Based on this special property, a fourfold degenerate nodal ring will emerge on the  $k_x$ - $k_y$  plane if one can realize a fourfold degenerate point along any radial direction (say,  $k_y$  direction). In order to realize the above scheme, we start from the case of a quarter-wave stack, i.e.,  $n_A d_A = n_B d_B$ . Figure 1e shows the s-polarized (dashed orange lines) and p-polarized (solid blue lines) bands along the  $k_z$  direction and  $k_y$  direction. In the band structure along the  $k_z$  direction ( $k_y = 0$ ), s-polarized and p-polarized bands are degenerate due to rotational symmetry. Furthermore, one can see that the second photonic band gap vanishes at  $k_z = 0$  (highlighted by the green circle).<sup>27</sup> This special property induces a fourfold degenerate point at the  $\Gamma$  point. Figure 1h shows the 3D band structures on the  $k_z = 0$  plane. For a better view of the degeneracy, only three-quarters of the bands are shown. One can see that the



**Figure 2.** Dual-polarization ridge photonic crystals. (a) Unit cell of dual-polarization RPC<sub>1</sub>. (b) Bulk band structure of RPC<sub>1</sub> along the  $k_y$  direction. Note that a partial gap opened in the vicinity of the original nodal ring. (c,d) Localized Berry vortices for (c) s-polarized and (d) p-polarized lower bands in (b). The insets show the cross-sectional views of the Berry curvature.

fourfold degenerate point is actually a quadratic Dirac point (QDP).<sup>28</sup> Then, we can deform this QDP into a Dirac nodal ring (DNR) by breaking the quarter-wave stack condition. To be specific, we change the thickness of each layer so that the quarter-wave stack condition is not satisfied any more, i.e.,  $n_A d_A > n_B d_B$  or  $n_A d_A < n_B d_B$ . For the case of  $n_A d_A > n_B d_B$ , we choose a 1D PC with  $d_A = 0.34a$  and  $d_B = 0.66a$  as an example. Figure 1d shows the calculated band structure of this 1D PC. Compared with Figure 1e, the original fourfold degeneracy is lifted and a band gap emerges. On the other hand, for the case of  $n_A d_A < n_B d_B$ , we choose  $d_A = 0.29a$  and  $d_B = 0.71a$  as an example. As highlighted by the purple circle in Figure 1f, the original four-band crossing point at  $k_y = 0$  is moved to  $k_y = 0.38 \times 2\pi/a$ . Since the 1D PC is rotation invariant on the  $xy$ -plane, this fourfold degenerate point extrudes along the azimuthal direction, forming a ring of double Dirac points [purple in Figure 1i]. For the dual-polarization DNR, its effective Hamiltonian can be written as

$$H = [v_x q_z \sigma_x + (v_0 \sigma_0 + v_z \sigma_z) q_r] \tau_0 \quad (1)$$

where  $\sigma_i$  is the Pauli matrix,  $\tau_0$  is the identity matrix, and  $q_z$  and  $q_r$  represent the normalized wavevector along  $z$  and radial directions, respectively (see more details in Note S6). Here,  $\tau_0$  acts on the pseudospin (i.e., polarization) subspace. For each polarization, the effective Hamiltonian resembles a type-II Weyl nodal ring's Hamiltonian, indicating that it carries the  $\pi$  Berry phase.<sup>29</sup> In a condensed matter system, nodal rings are sensitive to spin–orbit coupling because spin–orbit coupling can induce hybridization between opposite spin components.<sup>30</sup> In our photonic system, the polarization degree of freedom, rather than spin, is used to construct a double nodal ring. The coupling between s- and p-polarized states is naturally avoided. Since 1D PC possesses continuous rotational symmetry in the  $x$ - $y$  plane, one can always define two sets of decoupled modes (s polarized and p polarized). Therefore, the usual sensitivity of nodal rings to spin–orbit coupling is avoided in this work.

This double nodal ring is actually composed of two single nodal rings (for p and s polarizations) occurring exactly at the same momentum and frequency. The existence of these 4-fold degeneracies (QDP and DNR) can be explained by the absentee layer condition in thin-film optics. The characteristic matrix of each layer can be expressed as<sup>31,32</sup>

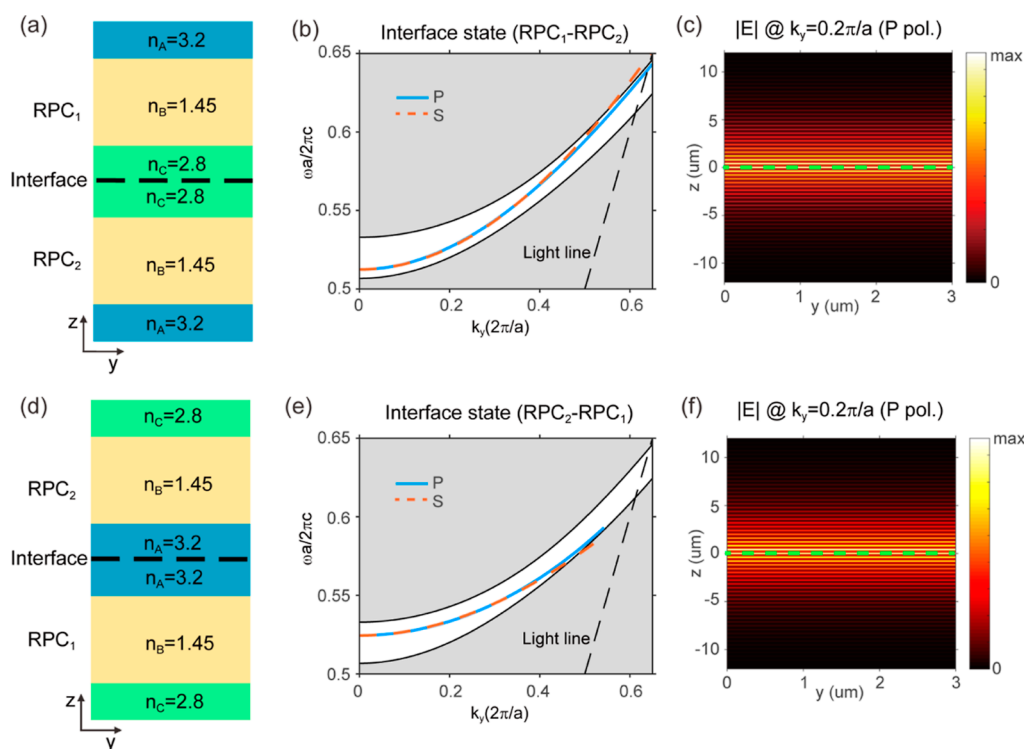
$$M_j = \begin{bmatrix} \cos \delta_j & i \sin \delta_j / \eta_j \\ i \eta_j \sin \delta_j & \cos \delta_j \end{bmatrix} \quad (2)$$

where  $j = A$  or  $B$ .  $\delta_j$  and  $\eta_j$  are the phase thicknesses and optical admittances of each layer. The phase thickness is defined as  $\delta_j = k_0 n_j d_j \cos(\theta_j)$ , in which  $n_j$  and  $d_j$  are the refractive index and thickness of each layer; and  $\theta_j$  and  $k_0$  are the refraction angle

and wavenumber in vacuum. Optical admittance is expressed as  $\eta_j = n_j / \cos(\theta_j)$  for s polarization and  $\eta_j = n_j \cos(\theta_j)$  for p polarization. When the phase thickness of one layer is integer times  $\pi$  ( $\delta_j = m\pi$ ), it is an absentee layer for the waves at that frequency. In this case, the characteristic matrix in eq 2 becomes an identity matrix, which means that the existence of the absentee layer should not affect the reflectance or transmittance as if it is absent. Especially, when both layer A and layer B satisfy absentee layer condition (i.e.,  $\delta_A = m_1 \pi$  and  $\delta_B = m_2 \pi$ ) at some frequency and some  $k_r$ , the whole crystal is effectively absent for both polarization waves, resulting in band gap closing and a 4-fold degeneracy. Note that this statement from the perspective of absentee layer condition coincides with the double nodal ring conditions provided in ref 26, which explains the existence of the dual-polarization nodal ring by the requirement on the ratio between two layers' optical paths. Based on this condition, we can design a dual-polarization nodal ring at any specific  $\omega$  and  $k_r$ . Using the relation  $k_r = n_j k_0 \cos(\theta_j)$ , we have the phase thickness  $\delta_j = k_0 d_j \sqrt{n_j^2 - k_r^2 / k_0^2}$ . After some algebra, the absentee layer condition reads

$$\left( \frac{\omega a}{2\pi c} \right)^2 - \left( \frac{k_r a}{2\pi n_j} \right)^2 = (m a / 2 n_j d_j)^2 \quad (3)$$

We plot the  $\omega - k_r$  hyperbolas at which the absentee layer condition is satisfied, with black thin (thick) dashed curves for layer A (B) in Figure 1d–f. From Figure 1e,f, it is clear that the black thin dashed curve and the black thick dashed curve exactly cross at the 4-fold degenerate point. Besides, we emphasize that eq 3 provides a clear guidance to tune the position of these 4-fold degenerate points. According to eq 3, one can tune the cross position or even remove the crossing point of these curves by tuning the refractive index or layer thickness of each layer. It should be noted that the physical mechanism in this work is different from that in ref 22. The single nodal ring in ref 22 is due to the p-polarized band gap closing at the Brewster angle between two constituent dielectrics. Note that the Brewster effect is polarization dependent and a similar total transmission phenomenon does not occur for s polarization, regardless of the structural/material parameters, unless considering magnetic materials with  $\mu_r \neq 1$ . Thus, a dual-polarization nodal ring cannot be achieved by simply tuning 1D PC's parameters. Here, the scheme to achieve a dual-polarization nodal ring is based on the concepts of the absentee layer, which is a polarization-independent effect. Furthermore, this type of 4-fold degeneracy is robust against parameters' perturbations. Figure 1j–l shows the in-plane dispersions for three different filling ratios, where s- and p-polarized bands always cross at the same frequency and wavevector. It indicates that this is not an



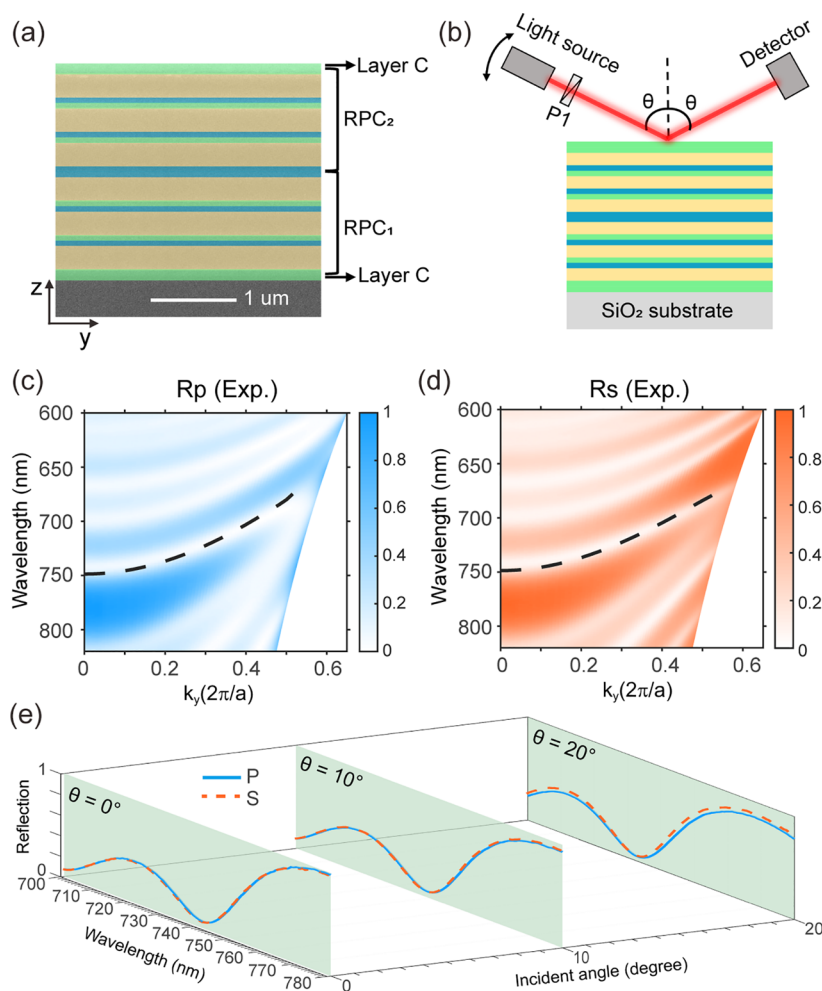
**Figure 3.** Dual-polarization ridge interface states. (a) Schematic of the RPC<sub>1</sub>–RPC<sub>2</sub> domain wall. (b) P-polarized (light-blue solid lines) and s-polarized (orange dashed lines) projected bands of the RPC<sub>1</sub>–RPC<sub>2</sub> domain wall. The dashed line represents the light line of air. Interface states emerge in the gap due to the opposite Berry vortices of two RPCs. (c) Electric field's magnitude of the p-polarized ridge interface state at  $k_y = 0.2\pi/a$ . The green dashed line highlights the position of the interface. (d–f) Similar to (a–c), but for the RPC<sub>2</sub>–RPC<sub>1</sub> domain wall.

accidental degeneracy by adjusting appropriate parameters. From the perspective of symmetry, this degeneracy between s-band crossing and p-band crossing is not guaranteed by spatial/time-reversal symmetry and is somewhat exotic. Usually, symmetry-protected degeneracy would happen along/on the symmetric  $k$ -line/plane. The absentee-layer-induced degeneracy only occurs at a nonsymmetric  $k_r$  or incident angle, while the s- and p-polarized bands split away from the crossing point with different slopes (group velocities).

Our previous work has demonstrated that the nodal ring can transit to topologically nontrivial ridge states by breaking inversion symmetry.<sup>22</sup> Here, we choose to replace the bottom layer A by a layer C with a refractive index of 2.8 (Figure 2a) and named it ridge photonic crystal1 (RPC<sub>1</sub>). For RPC<sub>1</sub>, since the absentee layer condition cannot be simultaneously satisfied for all three layers, the original double DNR degeneracy is lifted in Figure 2b. It should be noted that in ref 26, the authors focus on the study of gapless nodal ring states (without a topological band gap), rather than gapped ridge states. To investigate the topological property of these ridge bulk states, the Berry curvatures for the bands below the gap are calculated in Figure 2c,d for s-polarized and p-polarized bands. The insets show a zoomed-in view of the Berry curvature on the cut plane of  $k_y = 0$ , where Berry curvatures are localized around the  $k_z = 0$  plane. A toroidal-shaped Berry flux flows in the counter-clockwise direction for both polarizations. Alternatively, one can instead replace the top layer A by a layer C (named RPC<sub>2</sub>). Because RPC<sub>1</sub> and RPC<sub>2</sub> are inversion partners of each other, they have identical bulk band dispersions, but the band topologies of RPC<sub>1</sub> and RPC<sub>2</sub> are different. Berry vortices of RPC<sub>2</sub> flow in the opposite direction to that of RPC<sub>1</sub>, see more details in Supplementary Figure S3.

In the 2D photonic system, Dirac cones can be gapped by inversion symmetry breaking, which results in the gapped photonic valley states.<sup>33–36</sup> Nodal rings can be deemed as the extrusion of 2D Dirac points along a closed loop. By breaking the nodal ring, the resulting ridge states can be considered as the 3D version of the valley states. Therefore, these opposite topological features of RPC<sub>1</sub> and RPC<sub>2</sub> guarantee the existence of the ridge interface state in the domain wall formed by RPC<sub>1</sub> and RPC<sub>2</sub>. Note that researchers have studied interface states between 1D PCs and metals, which are well known as optical Tamm states.<sup>37–39</sup> The formation of an optical Tamm state can be attributed to the fact that the reflection phase of the metal (usually negative) exactly compensates with the one of 1D PC (positive). Likewise, the existence of ridge interface states between two topologically distinct RPCs is due to a similar resonance condition (see Figure S6). The only difference is that the compensation between RPC<sub>1</sub> and RPC<sub>2</sub> is guaranteed by their distinct Berry curvatures, which has been demonstrated in our previous work.<sup>22</sup> We first consider the RPC<sub>1</sub>–RPC<sub>2</sub> domain wall, where RPC<sub>1</sub> is on the top of RPC<sub>2</sub>, as sketched in Figure 3a. In the calculated projected bands of Figure 3b, two interface bands reside in the gap for both s polarization (orange dashed line) and p polarization (light-blue solid line). Note that the s-polarized and p-polarized ridge interface states propagate in the same direction because the Berry curvatures of the s-polarized band and p-polarized band flow in the same direction for RPC<sub>1</sub> (RPC<sub>2</sub>). Moreover, the s-polarized and p-polarized ridge interface states are degenerate almost in the whole band gap, which is hard to realize in other dielectric waveguide systems, because optical material's response to electric field and magnetic field is usually different. Since the absentee layer conditions are broken for RPCs, the





**Figure 4.** Experimental observation of dual-polarization ridge interface states. (a) Scanning electron microscopy image of the sample. (b) Experimental setup;  $P_1$ , polarizer. (c,d) Experimental measured angle-resolved reflection spectra for p polarization and s polarization. Calculated dispersions of ridge interface states (dashed lines) coincide with the reflection dips, demonstrating the existence of dual-polarization ridge interface states. (e) P-polarized (light-blue solid line) and s-polarized (orange dashed line) reflection spectra when the incident angle  $\theta = 0^\circ$ ,  $10^\circ$ , and  $20^\circ$ .

interface states are not exactly degenerate over the whole band gap. But thanks to the similar topological features (reflection phase winding) for s and p polarizations (see Figure S6), the s- and p-polarized interface bands are nearly degenerate in the whole band gap. As an example, Figure 3c shows the electric field of the p-polarized ridge interface state at  $k_y = 0.2\pi/a$ , where the green dashed line highlights the position of the interface. One can see that the electric field is tightly localized near the interface. Alternatively, one can also construct an interface by placing  $RPC_2$  on the top of  $RPC_1$ , i.e., the  $RPC_2$ – $RPC_1$  domain wall [Figure 3d]. As expected, there are also interface states in the band gap for both polarizations; see Figure 3d. Similar to the dispersion of the  $RPC_1$ – $RPC_2$  domain wall, the s-polarized and p-polarized ridge interface states are also degenerate almost in the whole band gap. P-polarized and s-polarized interface states are degenerate in the frequency range  $(0.5125, 0.559)*c/a$ , with a relative bandwidth of 8.7%, which is beneficial for achieving a polarization-independent filter whose working frequency can be tuned in a wide frequency range by adjusting an appropriate incident angle.<sup>40</sup> Interestingly, these interface states carry transverse spin, which enable unidirectional excitation of interface states (see more details in Figure S5). Interface states of ridge photonic crystals can be modulated by using phase change

materials<sup>41</sup> or soft materials.<sup>42</sup> Topologically protected interface states can survive even when the refractive indices of the materials deviate in a wide range, until the original DNR with finite radius shrinks to a point (see more details in Figure S4).

In order to observe dual-polarization ridge interface states in the experiment, we fabricated samples using an inductively coupled plasma-enhanced chemical vapor deposition (ICP-CVD) system (Oxford Instruments PlasmaPro System 100). Layer B is realized by depositing a  $SiO_2$  film with a thickness of 274 nm. For layers A and C, we deposited two kinds of silicon-rich nitride films ( $SRN_1$  and  $SRN_2$ ) with a thickness of 61 nm. Different refractive indices of  $SRN_1$  and  $SRN_2$  can be achieved by tuning the ratio between  $SiH_4/N_2$  during the deposition process. Optical constants of  $SRN_1$  and  $SRN_2$  are measured in Supplementary Figure S1. Figure 4a shows the scanning electron microscopy image of an  $RPC_2$ – $RPC_1$  domain wall, which is composed of 3-period  $RPC_2$  and 3-period  $RPC_1$ . Besides, to avoid the disturbance from redundant trivial interface states [between  $RPC_2$  and air, or between  $RPC_1$  and substrate ( $n = 1.45$ )], two extra layers of layer C are added on the top and the bottom of the domain wall structure (see more details in Figure S2). To demonstrate the existence of a ridge interface state, angle-resolved reflection spectra of the sample were measured using the experimental setup in Figure 4b.

Figure 4c,d shows the measured reflection spectra for p and s polarization, respectively. High-reflectivity regions agree well with the projected band. Black dashed lines represent the calculated dispersion of the interface state. As expected, a line of reflection dip exists for both p-polarized and s-polarized spectra, confirming the existence of the ridge interface state.

Interestingly, from Figure 3e, we find that p- and s-polarized ridge interface states are degenerate in a broad frequency range. This can be utilized for the polarization-independent optical filter whose working frequency can be tuned in a wide range. For instance, we plot the reflection spectra when the incident angle  $\theta = 0^\circ$ ,  $10^\circ$ , and  $20^\circ$  in Figure 4e. In the case of  $\theta = 10^\circ$ , the dips of p-polarized (light-blue solid line) and s-polarized (orange dashed line) reflection spectra both locate at the wavelength of 740 nm. Even when the incident angle varies from  $10^\circ$  to  $20^\circ$ , the dips in both spectra still locate at the same wavelength of 733 nm.

## CONCLUSIONS

In conclusion, we point out that absentee layer conditions can provide clear guidance to design a dual-polarization nodal ring in a simple 1D PC. By perturbing the absentee layer condition, the gapless nodal ring states transit to nontrivial gapped ridge states. In the domain wall formed by two RPCs with opposite Berry vortexes, ridge interface states emerge for both polarizations, and they are degenerate almost in the whole band gap. Compared with the single-polarization ridge interface state, our scheme relaxes the polarization constraint and makes it possible to realize dual-polarization photonic devices based on 1D PC, such as polarization-independent angularly selective optical filters, which can be utilized for high-efficiency solar energy conversion<sup>43,44</sup> and privacy screen.<sup>45</sup> By stacking a series of similar 1D PCs with different scaling factors, a cascaded PC can serve as an angular filter, enabling high conversion efficiency and privacy screen.<sup>46</sup>

## MATERIALS AND METHODS

**Numerical Simulation.** The bulk bands of 1D photonic crystals were calculated by MIT photonic bands (MPBs).<sup>47</sup> The interface states' dispersion and field patterns were calculated by COMSOL Multiphysics. All of the reflection spectra were calculated by the transfer matrix method.

**Sample Fabrication.** The sample shown in Figure 4a was fabricated by an ICP-CVD system (Oxford Instruments PlasmaPro System 100) on a quartz substrate. The deposition rate was  $12.4 \text{ nm min}^{-1}$  for the  $\text{SiO}_2$  layer. The different refractive indices of SRN were achieved by changing the ratio of  $\text{SiH}_4/\text{N}_2$  during the process of deposition. The deposition rate was  $6.8 \text{ nm min}^{-1}$  for the  $\text{SRN}_1$  layer and  $9.2 \text{ nm min}^{-1}$  for the  $\text{SRN}_2$  layer.

**Optical Measurements.** The refractive index and extinction coefficient of  $\text{SRN}_1$  and  $\text{SRN}_2$  were determined from spectrometry ellipsometry measurements (Sentech SE400). Angle-resolved reflection spectra of the sample were measured by an angle-resolved spectrometer (R1-UV, Ideaoptics, China).

## ASSOCIATED CONTENT

### Supporting Information

The Supporting Information is available free of charge at <https://pubs.acs.org/doi/10.1021/acsp Photonics.4c00248>.

Optical constants of silicon-rich nitride, interface states residing in the  $\text{RPC}_2$ –air interface or  $\text{RPC}_1$ –substrate interface, bulk band and Berry curvature of  $\text{RPC}_2$ , interface states in the  $\text{RPC}_1$ – $\text{RPC}_2$  domain wall for  $n_c$  with different values, transverse spin in the interface states, effective Hamiltonian of dual-polarization Dirac nodal ring, and reflection phases of RPCs (PDF)

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### Author Contributions

Z.-M.C. and L.-H.J. contributed equally to this work. W.D. and W.C. conceived the idea. L.-H.J. and W.D. performed the numerical simulations. L.-H.J. derived eq 3. Z.-M.C. fabricated the samples. Z.-M.C. and W.D. performed the optical measurements. All authors contributed to the analysis of the results. W.D., W.C., S.J., and J.D. wrote the manuscript with input from other authors. W.C. and J.D. supervised the project. All authors have given approval to the final version of the manuscript.

### Notes

The authors declare no competing financial interest.

## ACKNOWLEDGMENTS

This work was supported by the National Key Research and Development Program of China (grant no. 2022YFA1404304), National Natural Science Foundation of China (grant no. 12204552), and Guangdong Basic and Applied Basic Research Foundation (grant no. 2023B1515040023).

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